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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HD74ALVCH16721

3.3-V 20-bit Flip Flops with 3-state Outputs



ADE-205-139B (Z)
3rd. Edition
December 1999

Description

The HD74ALVCH16721's twenty flip flops are edge triggered D-type flip flops with qualified clock storage. On the positive transition of the clock (CLK) input, the device provides true data at the Q outputs, provided that the clock enable ($\overline{\text{CLKEN}}$) input is low. If $\overline{\text{CLKEN}}$ is high, no data is stored. A buffered output enable ($\overline{\text{OE}}$) input can be used to place the twenty outputs in either a normal logic state (high or low level) or a high impedance state. In the high impedance state, the outputs neither load nor drive the bus lines significantly. The high impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components. The output enable ($\overline{\text{OE}}$) input does not affect the internal operation of the flip flops. Old data can be retained or new data can be entered while the outputs are in the high impedance state. Active bus hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

Features

- $V_{\text{CC}} = 2.3 \text{ V to } 3.6 \text{ V}$
- Typical V_{OL} ground bounce $< 0.8 \text{ V}$ ($@V_{\text{CC}} = 3.3 \text{ V, Ta} = 25^\circ\text{C}$)
- Typical V_{OH} undershoot $> 2.0 \text{ V}$ ($@V_{\text{CC}} = 3.3 \text{ V, Ta} = 25^\circ\text{C}$)
- High output current $\pm 24 \text{ mA}$ ($@V_{\text{CC}} = 3.0 \text{ V}$)
- Bus hold on data inputs eliminates the need for external pullup / pulldown resistors

Function Table

Inputs				Output Q
\overline{OE}	\overline{CLKEN}	CLK	D	
L	H	X	X	Q_0^{*1}
L	L	↑	H	H
L	L	↑	L	L
L	L	L or H	X	Q_0^{*1}
H	X	X	X	Z

H : High level

L : Low level

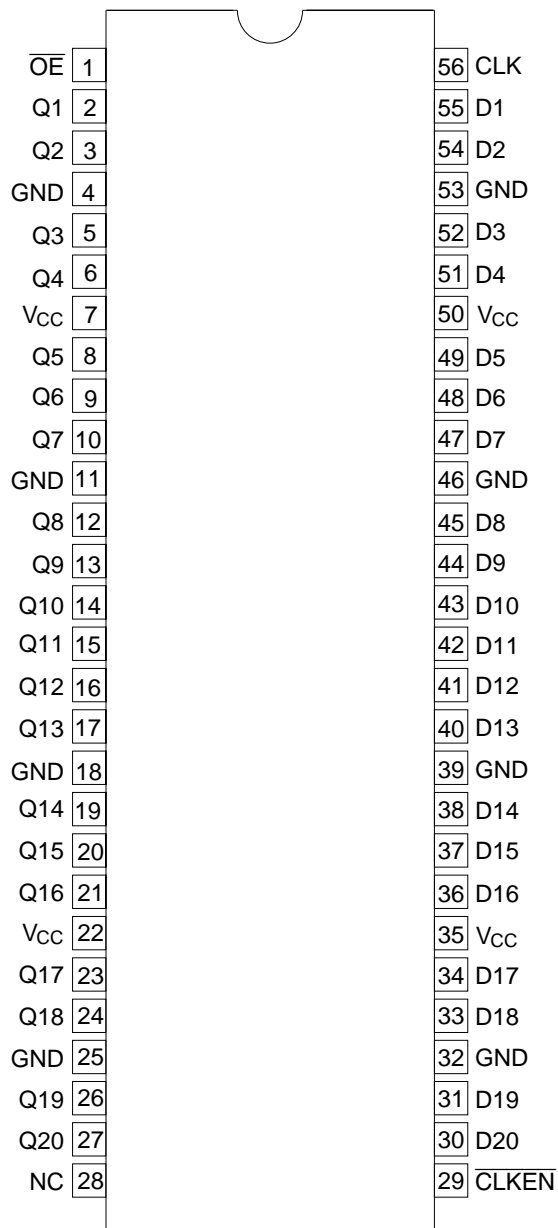
X : Immaterial

Z : High impedance

↑ : Low to high transition

Note: 1. Output level before the indicated steady state input conditions were established.

Pin Arrangement



(Top view)

Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V_{CC}	-0.5 to 4.6	V	
Input voltage ¹	V_I	-0.5 to 4.6	V	
Output voltage ^{*1,2}	V_O	-0.5 to $V_{CC} + 0.5$	V	
Input clamp current	I_{IK}	-50	mA	$V_I < 0$
Output clamp current	I_{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	I_O	±50	mA	$V_O = 0$ to V_{CC}
V_{CC} , GND current / pin	I_{CC} or I_{GND}	±100	mA	
Maximum power dissipation at $T_a = 55^\circ\text{C}$ (in still air) ^{*3}	P_T	1	W	TSSOP
Storage temperature	T_{stg}	-65 to 150	°C	

Notes: Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

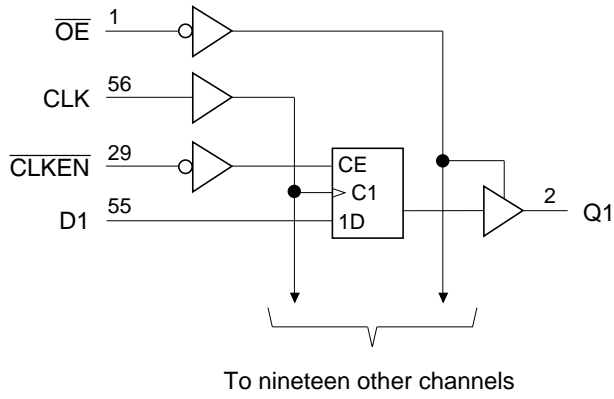
1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	V_{CC}	2.3	3.6	V	
Input voltage	V_I	0	V_{CC}	V	
Output voltage	V_O	0	V_{CC}	V	
High level output current	I_{OH}	—	-12	mA	$V_{CC} = 2.3\text{ V}$
		—	-12		$V_{CC} = 2.7\text{ V}$
		—	-24		$V_{CC} = 3.0\text{ V}$
Low level output current	I_{OL}	—	12	mA	$V_{CC} = 2.3\text{ V}$
		—	12		$V_{CC} = 2.7\text{ V}$
		—	24		$V_{CC} = 3.0\text{ V}$
Input transition rise or fall rate	$\Delta t / \Delta v$	0	10	ns / V	
Operating temperature	T_a	-40	85	°C	

Note: Unused control inputs must be held high or low to prevent them from floating.

Logic Diagram



Electrical Characteristics (Ta = -40 to 85°C)

Item	Symbol	V _{CC} (V) ^{*1}	Min	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.3 to 2.7	1.7	—	V	
		2.7 to 3.6	2.0	—		
	V _{IL}	2.3 to 2.7	—	0.7		
		2.7 to 3.6	—	0.8		
Output voltage	V _{OH}	Min to Max	V _{CC} -0.2	—	V	I _{OH} = -100 μA
		2.3	2.0	—		I _{OH} = -6 mA, V _{IH} = 1.7 V
		2.3	1.7	—		I _{OH} = -12 mA, V _{IH} = 1.7 V
		2.7	2.2	—		I _{OH} = -12 mA, V _{IH} = 2.0 V
		3.0	2.4	—		I _{OH} = -12 mA, V _{IH} = 2.0 V
		3.0	2.0	—		I _{OH} = -24 mA, V _{IH} = 2.0 V
	V _{OL}	Min to Max	—	0.2		I _{OL} = 100 μA
		2.3	—	0.4		I _{OL} = 6 mA, V _{IL} = 0.7 V
		2.3	—	0.7		I _{OL} = 12 mA, V _{IL} = 0.7 V
		2.7	—	0.4		I _{OL} = 12 mA, V _{IL} = 0.8 V
		3.0	—	0.55		I _{OL} = 24 mA, V _{IL} = 0.8 V
Input current	I _{IN}	3.6	—	±5	μA	V _{IN} = V _{CC} or GND
		2.3	45	—		V _{IN} = 0.7 V
		2.3	-45	—		V _{IN} = 1.7 V
		3.0	75	—		V _{IN} = 0.8 V
		3.0	-75	—		V _{IN} = 2.0 V
		3.6	—	±500		V _{IN} = 0 to 3.6 V
Off state output current ^{*2}	I _{OZ}	3.6	—	±10	μA	V _{OUT} = V _{CC} or GND
Quiescent supply current	I _{CC}	3.6	—	40	μA	V _{IN} = V _{CC} or GND
	ΔI _{CC}	3.0 to 3.6	—	750	μA	V _{IN} = one input at (V _{CC} -0.6) V, other inputs at V _{CC} or GND

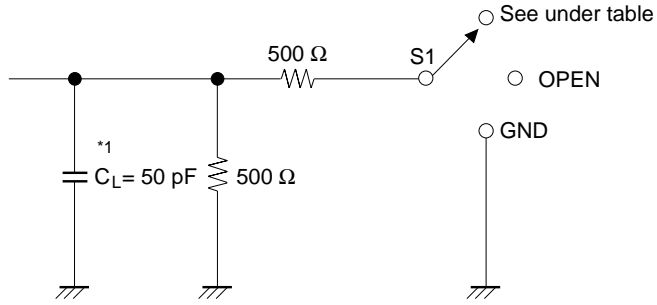
Notes: 1. For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

2. For I/O ports, the parameter I_{OZ} includes the input leakage current.

Switching Characteristics (Ta = -40 to 85°C)

Item	Symbol	V _{CC} (V)	Min	Typ	Max	Unit	FROM (Input)	TO (Output)
Maximum clock frequency	f _{max}	2.5±0.2	150	—	—	MHz		
		2.7	150	—	—			
		3.3±0.3	150	—	—			
Propagation delay time	t _{PLH} t _{PHL}	2.5±0.2	1.0	—	5.6	ns	CLK	Q
		2.7	1.0	—	5.1			
		3.3±0.3	1.0	—	4.3			
Output enable time	t _{ZH} t _{ZL}	2.5±0.2	1.0	—	6.1	ns	\overline{OE}	Q
		2.7	1.0	—	5.8			
		3.3±0.3	1.0	—	4.8			
Output disable time	t _{HZ} t _{LZ}	2.5±0.2	1.0	—	5.5	ns	\overline{OE}	Q
		2.7	1.0	—	4.7			
		3.3±0.3	1.0	—	4.4			
Setup time	t _{su}	2.5±0.2	4.0	—	—	ns	Data before CLK↑	
		2.7	3.6	—	—			
		3.3±0.3	3.1	—	—			
		2.5±0.2	3.4	—	—		\overline{CLKEN} before CLK↑	
		2.7	3.1	—	—			
		3.3±0.3	2.7	—	—			
Hold time	t _h	2.5±0.2	0	—	—	ns	Data after CLK↑	
		2.7	0	—	—			
		3.3±0.3	0	—	—			
		2.5±0.2	0	—	—		\overline{CLKEN} after CLK↑	
		2.7	0	—	—			
		3.3±0.3	0	—	—			
Pulse width	t _w	2.5±0.2	3.3	—	—	ns		
		2.7	3.3	—	—			
		3.3±0.3	3.3	—	—			
Input capacitance	C _{IN}	3.3	—	3.5	—	pF		
Output capacitance	C _O	3.3	—	7.0	—	pF		

• Test Circuit

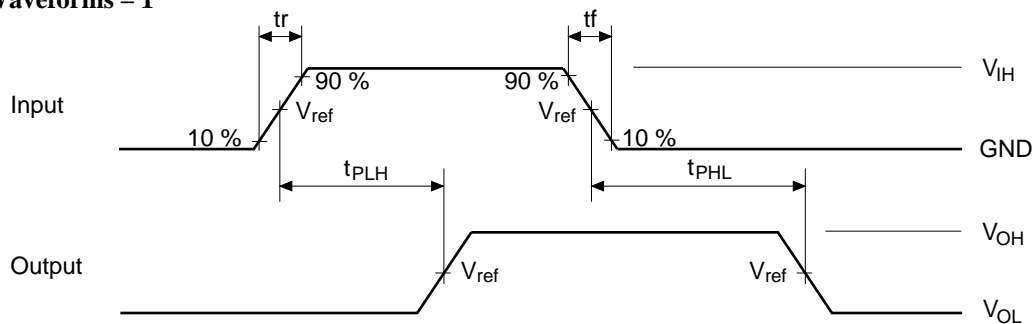


Load Circuit for Outputs

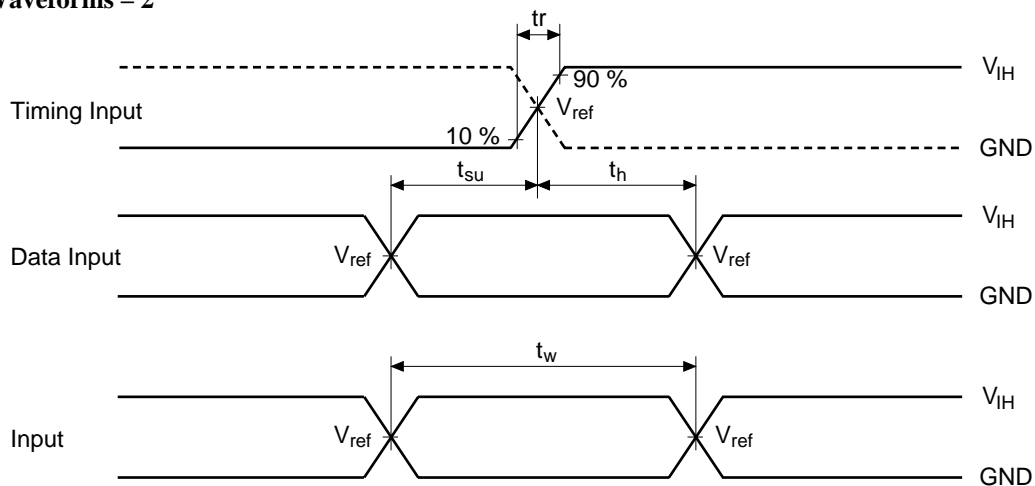
Symbol	V _{CC} =2.5±0.2V	V _{CC} =2.7V, 3.3±0.3V
t _{PLH} /t _{PHL}	OPEN	OPEN
t _{su} /t _h /t _w	OPEN	OPEN
t _{ZH} /t _{HZ}	GND	GND
t _{ZL} /t _{LZ}	4.6 V	6.0 V

Note: 1. C_L includes probe and jig capacitance.

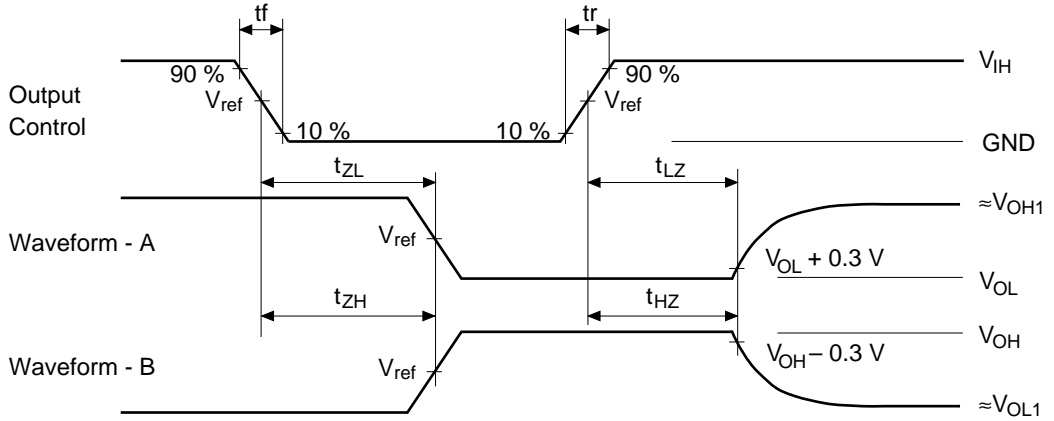
• Waveforms – 1



• Waveforms – 2



• Waveforms – 3

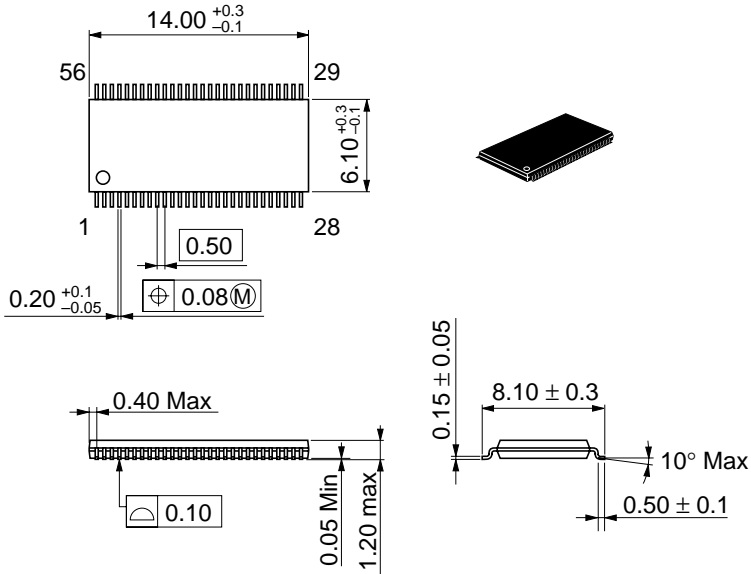


TEST	$V_{CC}=2.5\pm 0.2V$	$V_{CC}=2.7V,$ $3.3\pm 0.3V$
V_{IH}	2.3 V	2.7 V
V_{ref}	1.2 V	1.5 V
V_{OH1}	2.3 V	3.0 V
V_{OL1}	GND	GND

- Notes:
1. All input pulses are supplied by generators having the following characteristics:
 $PRR \leq 10$ MHz, $Z_o = 50 \Omega$, $t_r \leq 2.5$ ns, $t_f \leq 2.5$ ns.
 2. Waveform – A is for an output with internal conditions such that the output is low except when disabled by the output control.
 3. Waveform – B is for an output with internal conditions such that the output is high except when disabled by the output control.
 4. The output are measured one at a time with one transition per measurement.

Package Dimensions

Unit : mm



Hitachi code	TTP-56D
EIAJ code	—
JEDEC code	—

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